

# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	65	V
Gate-Source Voltage		$V_{GSS}$	±16	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	$T_C = +25$ °C $T_C = +70$ °C	I <sub>D</sub>	25.3 20.3	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	100	Α
Maximum Continuous Body Diode Forward Current (Note 6)		Is	25	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I <sub>SM</sub>	100	Α
Avalanche Current, L = 0.1mH		I <sub>AS</sub>	19	А
Avalanche Energy, L = 0.1mH		E <sub>AS</sub>	18	mJ

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25$ °C	$P_{D}$	0.98	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{ hetaJA}$	127.9	°C/W
Total Power Dissipation (Note 6)	$T_A = +25$ °C	$P_{D}$	2.34	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{ heta JA}$	53.5	°C/W
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	5.9	°C/W
Operating and Storage Temperature Range		$T_{J}, T_{STG}$	-55 to +150	°C

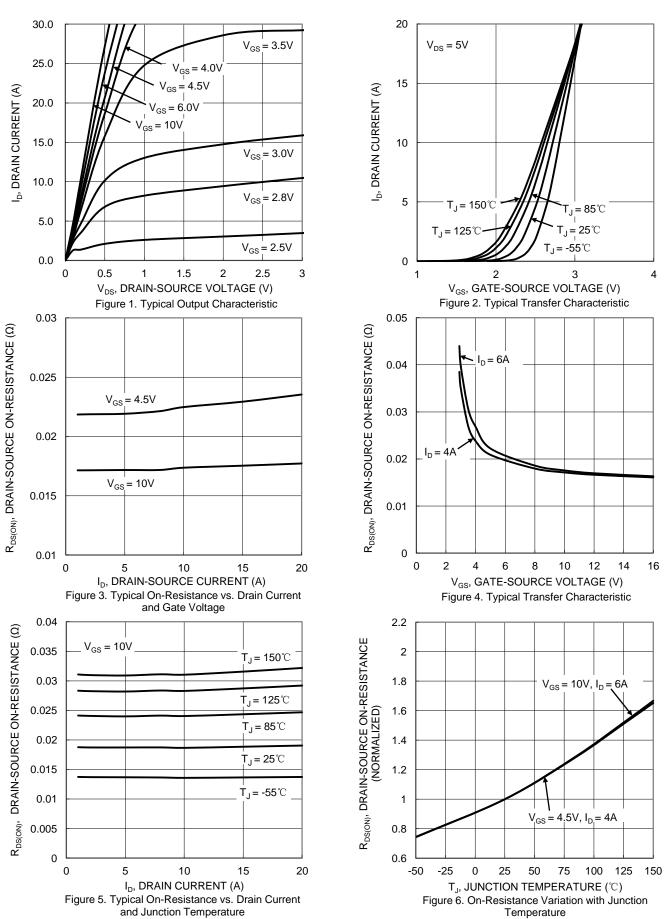
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

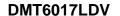
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	65	_	-	V	$V_{GS} = 0V$ , $I_D = 10mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±10	μΑ	$V_{GS} = \pm 12.8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	1	_	2.3	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	2	_	17.5	22	mΩ	$V_{GS} = 10V, I_D = 6A$	
Static Dialii-Source Off-Resistance	R <sub>DS(ON)</sub>	_	22.3	29		$V_{GS} = 4.5V, I_D = 4A$	
Diode Forward Voltage	$V_{SD}$	_	0.7	1	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	891	-	pF	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	Coss	_	223		pF		
Reverse Transfer Capacitance	Crss	_	29	1	pF		
Gate Resistance	$R_g$	_	1.57	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_g$	_	7.5	1	nC	V <sub>DS</sub> = 30V, I <sub>D</sub> = 6A	
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$	_	15.3	1	nC		
Gate-Source Charge	$Q_{gs}$	_	1.8	1	nC		
Gate-Drain Charge	Q <sub>qd</sub>	_	3.1	_	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	4.0	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	5.9	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$ $R_g = 3.3\Omega, I_D = 6A$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	11.7	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	3.3		ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	21.1	_	ns	I <sub>F</sub> = 6A, di/dt = 100A/µs	
Body Diode Reverse Recovery Charge	$Q_{RR}$	_	11.9	_	nC		

5. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.

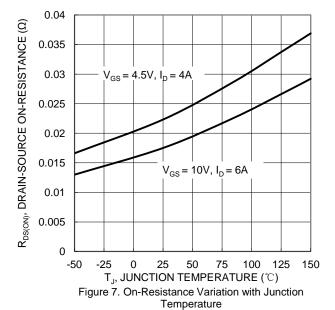
Bevice mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

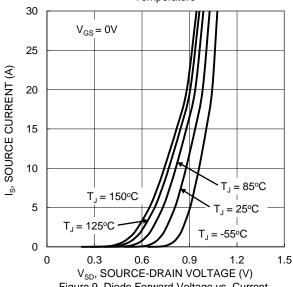


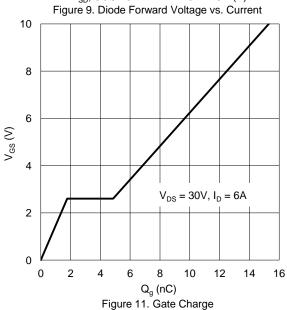


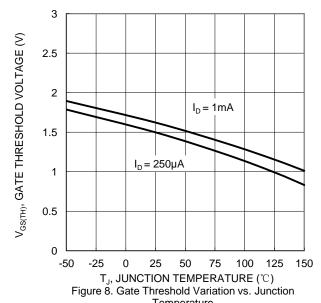


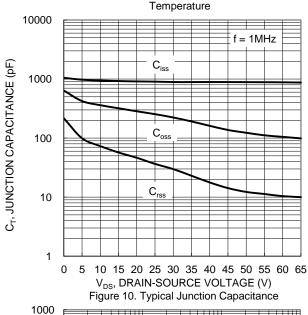


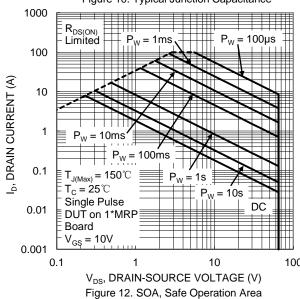












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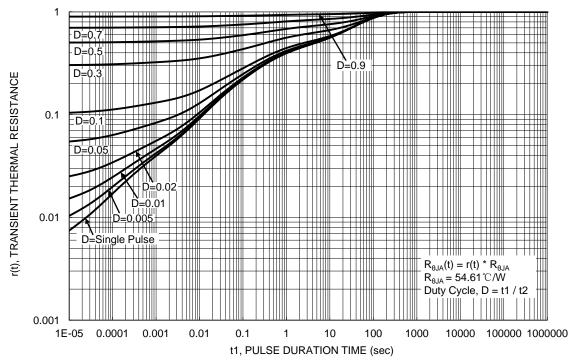


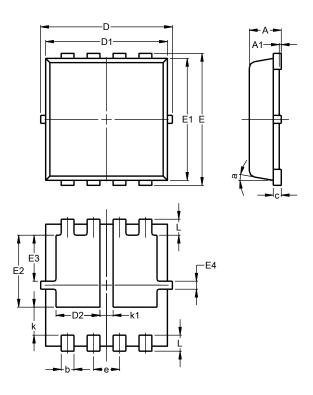
Figure 13. Transient Thermal Resistance



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8 (Type UXC)

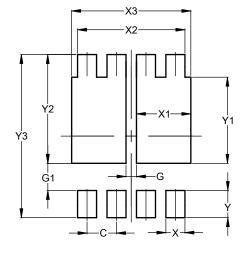


PowerDI3333-8						
(Type UXC)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
<b>A</b> 1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	0.90	1.30	1.10			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
L	0.30	0.50	0.40			
k	0.50	0.90	0.70			
k1	0.13	0.53	0.33			
а	0°	12°	10°			
All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (Type UXC)



Dimensions	Value (in mm)			
С	0.650			
G	0.230			
G1	0.600			
Х	0.420			
X1	1.200			
X2	2.370			
Х3	2.630			
Υ	0.600			
Y1	1.900			
Y2	2.400			
Y3	3.600			



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